

### PMV22EN,215 Information



For Reference Only

Part Number PMV22EN,215

Manufacturer NXP

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 30V 5.2A SOT23

**Package** TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









## PMV22EN,215 Specifications

Manufacturer Part Number         PMV22EN,215           Manufacturer         NXP           Category         Discrete Semiconductor Products           Fackage         TC-236-3, SC-59, SOT-23-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         5.2A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         13nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         480pF @ 15V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         510mW (Ta)           Rds On (Max) @ Id, Vgs         22 mOhm @ 5.2A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-236-3, SC-59, SOT-23-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         5.2A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         13nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         480pF @ 15V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         510mW (Ta)           Rds On (Max) @ Id, Vgs         22 mOhm @ 5.2A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)	Manufacturer Part Number	PMV22EN,215
Transistors - FETs, MOSFETs - Single         Package       TO-236-3, SC-59, SOT-23-3         Series       -         FET Type       N-Channel         Technology       MOSFET (Metal Oxide)         Drain to Source Voltage (Vdss)       30V         Current - Continuous Drain (Id) @ 25°C       5.2A (Ta)         Drive Voltage (Max Rds On, Min Rds On)       4.5V, 10V         Vgs(th) (Max) @ Id       2.5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       13nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       480pF @ 15V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       510mW (Ta)         Rds On (Max) @ Id, Vgs       22 mOhm @ 5.2A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)	Manufacturer	NXP
Package       TO-236-3, SC-59, SOT-23-3         Series       -         FET Type       N-Channel         Technology       MOSFET (Metal Oxide)         Drain to Source Voltage (Vdss)       30V         Current - Continuous Drain (Id) @ 25°C       5.2A (Ta)         Drive Voltage (Max Rds On, Min Rds On)       4.5V, 10V         Vgs(th) (Max) @ Id       2.5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       13nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       480pF @ 15V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       510mW (Ta)         Rds On (Max) @ Id, Vgs       22 mOhm @ 5.2A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)	Category	Discrete Semiconductor Products
Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         5.2A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         13nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         480pF @ 15V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         510mW (Ta)           Rds On (Max) @ Id, Vgs         22 mOhm @ 5.2A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)		Transistors - FETs, MOSFETs - Single
FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  5.2A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  N-Channel  1004  4.5V, 10V  4.5V, 10V  4.5V, 10V  4.5V, 10V  4.5V, 10V  480pF @ 15V  480pF @ 15V  480pF @ 15V  510mW (Ta)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)	Package	TO-236-3, SC-59, SOT-23-3
Technology Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 5.2A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 13nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 480pF @ 15V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 22 mOhm @ 5.2A, 10V Operating Temperature55°C ~ 150°C (TJ)	Series	-
Drain to Source Voltage (Vdss)       30V         Current - Continuous Drain (Id) @ 25°C       5.2A (Ta)         Drive Voltage (Max Rds On, Min Rds On)       4.5V, 10V         Vgs(th) (Max) @ Id       2.5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       13nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       480pF @ 15V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       510mW (Ta)         Rds On (Max) @ Id, Vgs       22 mOhm @ 5.2A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C       5.2A (Ta)         Drive Voltage (Max Rds On, Min Rds On)       4.5V, 10V         Vgs(th) (Max) @ Id       2.5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       13nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       480pF @ 15V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       510mW (Ta)         Rds On (Max) @ Id, Vgs       22 mOhm @ 5.2A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) $4.5V, 10V$ $Vgs(th)$ (Max) @ Id $2.5V$ @ $250\mu$ AGate Charge (Qg) (Max) @ Vgs $13nC$ @ $10V$ Input Capacitance (Ciss) (Max) @ Vds $480pF$ @ $15V$ $Vgs$ (Max) $\pm 20V$ FET Feature-Power Dissipation (Max) $510mW$ (Ta)Rds On (Max) @ Id, Vgs $22 mOhm$ @ $5.2A$ , $10V$ Operating Temperature $-55^{\circ}$ C ~ $150^{\circ}$ C (TJ)	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id       2.5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       13nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       480pF @ 15V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       510mW (Ta)         Rds On (Max) @ Id, Vgs       22 mOhm @ 5.2A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)	Current - Continuous Drain (Id) @ 25°C	5.2A (Ta)
Gate Charge (Qg) (Max) @ Vgs       13nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       480pF @ 15V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       510mW (Ta)         Rds On (Max) @ Id, Vgs       22 mOhm @ 5.2A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds       480pF @ 15V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       510mW (Ta)         Rds On (Max) @ Id, Vgs       22 mOhm @ 5.2A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)	Vgs(th) (Max) @ Id	2.5V @ 250µA
Vgs (Max) $\pm 20$ VFET Feature-Power Dissipation (Max) $510$ mW (Ta)Rds On (Max) @ Id, Vgs $22$ mOhm @ $5.2$ A, $10$ VOperating Temperature $-55$ °C ~ $150$ °C (TJ)	Gate Charge (Qg) (Max) @ Vgs	13nC @ 10V
FET Feature -  Power Dissipation (Max) 510mW (Ta)  Rds On (Max) @ Id, Vgs 22 mOhm @ 5.2A, 10V  Operating Temperature -55°C ~ 150°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	480pF @ 15V
Power Dissipation (Max) 510mW (Ta)  Rds On (Max) @ Id, Vgs 22 mOhm @ 5.2A, 10V  Operating Temperature -55°C ~ 150°C (TJ)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs       22 mOhm @ 5.2A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)	FET Feature	-
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Power Dissipation (Max)	510mW (Ta)
	Rds On (Max) @ Id, Vgs	22 mOhm @ 5.2A, 10V
Mounting Type Surface Mount	Operating Temperature	-55°C ~ 150°C (TJ)
	Mounting Type	Surface Mount
Supplier Device Package TO-236AB (SOT23)	Supplier Device Package	TO-236AB (SOT23)
Package / Case TO-236-3, SC-59, SOT-23-3	Package / Case	TO-236-3, SC-59, SOT-23-3
Report errors?		Report errors?

### PMV22EN,215 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## PMV22EN,215 Payment Methods









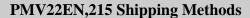
























If you have any question about PMV22EN,215, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com